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PATENT
0020-4666P

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IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Fumihiko KONUSHI et al. Conf.: 1396
Application No.: 09/492,803 Group: 2881
Filed: January 28, 2000 Examiner: Q. Leung
For: SEMICONDUCTOR LASER DEVICE AND METHOD
OF MANUFACTURING SAME

AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

November 1, 2001

Sir:

In reply to the Office Action dated August 1, 2001, the following remarks are respectfully submitted in the above-identified application.

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A semiconductor laser device having a quantum well active layer disposed between a pair of cladding layers, and an optical guide layer disposed between at least one of the cladding layers and the quantum well active layer, wherein a spacer layer is provided between said optical guide layer and said at least one of the cladding layers.

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